IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A composite substrate in which an electrode and a dielectric layer are successively formed on an electrically insulating substrate,

said substrate having a coefficient of thermal expansion of 10 to 20 ppm/K.

Claim 2 (Original): The composite substrate of claim 1 wherein said substrate is composed mainly of magnesia (MgO), steatite ($MgO \cdot SiO_2$) or forsterite ($2MgO \cdot SiO_2$).

Claim 3 (Currently Amended): The composite substrate of claim ~~1 or~~ 2 wherein said dielectric layer is a sintered ceramic body composed mainly of barium titanate ($BaTi0_3$).

Claim 4 (Original): The composite substrate of claim 3 wherein said dielectric layer contains one or more oxides selected from the group consisting of manganese oxide (MnO), magnesium oxide (MgO), tungsten oxide (WO_3), calcium oxide (CaO), zirconium oxide (ZrO_2), niobium oxide (Nb_2O_5) and cobalt oxide (Co_2O_3) .

Claim 5 (Original): The composite substrate of claim 3 wherein said dielectric layer contains the oxides of one or more elements selected from the group consisting of rare earth elements Sc, Y, La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu.

Claim 6 (Original): The composite substrate of claim 3 wherein said dielectric layer contains a vitreous component composed of silicon oxide (SiO_2).

Claim 7 (Original): An EL device comprising at least a light emitting layer and a second electrode on the composite substrate of claim 1.

Claim 8 (Original): The EL device of claim 7 further comprising a second insulator layer between the light emitting layer and the second electrode.

Claim 9 (Previously Presented): The composite substrate of claim 1, wherein said dielectric layer is a sintered ceramic body composed mainly of barium titanate ($BaTiO_3$).

Claim 10 (Previously Presented): The composite substrate of claim 1, wherein said substrate has a coefficient of thermal expansion of about 12 to 18 ppm/K.

Claim 11 (Previously Presented): The composite substrate of claim 2, wherein said substrate is composed mainly of magnesia.

Claim 12 (Currently Amended): The composite substrate of claim 1, wherein the electrode ~~is~~ comprises a metallic electrode ~~comprising~~ selected from the group consisting of palladium, rhodium, iridium, rhenium, ruthenium, platinum, silver, gold, tantalum, nickel, chromium ~~or~~ and titanium.

Claim 13 (Currently Amended): The composite substrate of claim 1, wherein the electrode ~~is~~ comprises a metallic electrode ~~comprising~~ selected from the group consisting of Pd, Pt, Au, Ag ~~or~~ and an alloy thereof.

Claim 14 (Previously Presented): The EL device of claim 7, wherein the second electrode is a transparent electrode of ITO or IZO.

Claim 15 (Previously Presented): The EL device of claim 14, wherein said ITO comprises a proportion of SnO_2 to In_2O_3 of from 1 to 20% by weight.

Claim 16 (Previously Presented): The EL device of claim 14, wherein said IZO comprises a proportion of ZnO to In_2O_3 of about 12 to 32% by weight.

Claim 17 (Previously Presented): The EL device of claim 14, wherein the second electrode is silicon-based.

Claim 18 (Currently Amended): The EL device of claim 17, wherein the silicon-based electrode ~~comprises~~ is selected from the group consisting of polycrystalline silicon (p-Si), amorphous silicon (a-Si) ~~or~~ and single crystal silicon.

Claim 19 (Previously Presented): The EL device of claim 17, wherein said silicon-based electrode comprises a dopant to impart conductivity.

Claim 20 (Currently Amended): The EL device of claim 19, wherein said dopant ~~comprises~~ is selected from the group consisting of B, P, ~~As~~, Sb ~~or~~ and Al in an amount of about 0.001 to 5 at.%.

Claim 21 (Previously Presented): The EL device of claim 14, wherein said second electrode has a resistivity of up to 1 Ω·cm.

Claim 22 (Previously Presented): The EL device of claim 21, wherein said second electrode has a resistivity of from about 0.003 to 0.1 Ω·cm.

Claim 23 (Previously Presented): The EL device of claim 7, wherein said light emitting layer comprises a phosphor.

Claim 24 (Previously Presented): The EL device of claim 23, wherein said phosphor is a sulfide phosphor.

Claim 25 (Previously Presented): The EL device of claim 24, wherein said sulfide phosphor is a ZnS phosphor.